NSN 5962-01-369-7740

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Maximum Power Dissipation Rating	:	
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1.1 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

An/fps-124

Features Provided:

Programmed and bipolar

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital bipolar programmable logic, monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 12.0 volts total supply

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

81349--38510/504 government specification and 56232-1219257 manufacturers source control

Specification Or Standard:

08 type and b class and r case and a finish and 202 number

Departure From Cited Designator:

Altered by programming marking & testing

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N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

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